In the Specification:

Please amend the title of the application as follows:

[[A]] NOVEL METHOD TO CONTROL SPACER WIDTH

Please replace the paragraph that begins on page 5, line 9 of the originally filed Specification with the following amended paragraph:

As shown in Fig. 1, a gate electrode portion 14 is formed over structure 10. An underlying gate oxide layer 12 is interposed between gate portion 14 and structure 10. A first spacer layer 16 is formed over the top and sidewalls of gate electrode portion 14 and includes an L shaped a spacer portion 18 that extends as at 17 from the gate electrode portion 14 sidewalls over along the structure 10. Oxide remnants 20, preferably LPTEOS as will be used for purposes of illustration hereafter, cover the sidewall portions of first spacer layer 16 as shown in Fig. 1.

Please replace the paragraph that begins on page 7, line 3 of the originally filed Specification with the following amended paragraph:

The (initial) width 22 of the <u>spacer portion 18 of the</u> first spacer layer 16 extending as at 17 from the gate electrode portion 14 is determined and compared to the <u>L-shaped</u> target spacer 32 width 30. <u>As shown in Fig. 2, the initial width 22 is defined by the amount the spacer portion 18 extends away from the gate electrode portion 14.</u> The difference <u>24</u> between the target spacer 32 width 30

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and the (initial) width 22 of spacer portion 18 is determined and this datum/data is fed-forward to determine the thickness 26 of [[the]] **a** second spacer layer 31 as shown in Fig. 3 and described below.

Please replace the paragraph that begins on page 7, line 10 of the originally filed Specification with the following amended paragraph:

Preferably, the (initial) width 22 of the <u>spacer portion 18 of the</u> first spacer layer 16 is intentionally formed <u>to be</u> less than the target spacer 32 width 30. The ability to precisely control the width 30 of the target/composite spacer 32 is possible through good thickness control of the second spacer layer/second SiN spacer layer 31.

Please replace the paragraph that begins on page 7, line 17 of the originally filed Specification with the following amended paragraph:

As shown in Fig. 3, using this feed-forward datum/data, the difference 24, a second spacer layer 31 is formed over the first spacer layer 16 and the structure 10 so that its thickness 26 that equals the difference 24 between the target spacer 32 width 30 and the (initial) width 22 of spacer portion 18. For example, if the target spacer 32 width 30 is 900Å (third column), than for the indicated (initial) width 22 of spacer portion 18 of the first spacer layer 16 (second column) as shown in the following table, the thickness 26 of the second spacer layer 31 would be as shown (second column).